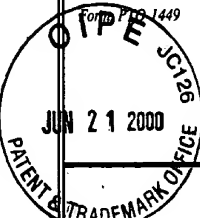


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U.S. PATENT DOCUMENTS

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AA	09/580,733		CEM BASCERI			05/26/00
AB	09/476,516		CEM BASCERI			01/03/00
AC						
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AF						
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AH						
AI						
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FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
AL	0 957 522 A2	17.11.99	EPO (MATSUSHITA ELECTRIC INDUSTRIAL)				
AM	0 855 735 A2	29.07.98	EPO (APPLIED MATERIALS, INC.)				
AN							
AO							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Vishnu K. Agarwal et al.		09/388063	
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>[Signature]</i>	AA	5,596,214	01/1997	ENDO	257	324	
	AB	5,783,253	07/1998	ROH	427	81	
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	AD						
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<i>[Signature]</i>	AF	CHOI, Y.C., et al., ABSTRACT, "Improvements of the properties of Chemical-Vapor-Deposited (Ba,Sr) TiO ₃ Films through Use of a Seed Layer", <u>Jpn. J. Appl. Phys.</u> , Part 1, Vol. 35, No. 11, pp. 6824-6828 (1997)					
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Jag	AF	EGUCHI, et al., ABSTRACT, "Chemical Vapor Deposition of (Ba,Sr)TiO ₃ Thin Films for Application in Gigabit Scale Dynamic Random Access Memories", <u>Integrated Ferroelectrics</u> , Vol. 14, No. 1-4, Pt. 1, pp. 33-42 (1997)					
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